**Product data sheet** 

## 1. Product profile

### 1.1 General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT428 (D-PAK) surface mounted package.

### 1.2 Features and benefits

- Low thermal resistance
- Fast switching

## 1.3 Applications

- Electronic lighting ballasts
- Inverters

- DC-to-DC converters
- Motor control systems

### 1.4 Quick reference data

- V<sub>CESM</sub> ≤ 700 V
- Arr P<sub>tot</sub>  $\leq$  80 W

- $I_C \le 4 A$
- h<sub>FEsat</sub> = 12.5 (typ)

# 2. Pinning information

Table 1. Pinning

	9		
Pin	Description	Simplified outline	Symbol
1	base	mb	С
2	collector	[1]	J
3	emitter		В
mb	mounting base; connected to collector		 E sym123
		SOT428 (D-PAK)	

<sup>[1]</sup> It is not possible to make a connection to pin 2 of the SOT428 (D-PAK) package.

# 3. Ordering information

Table 2. Ordering information

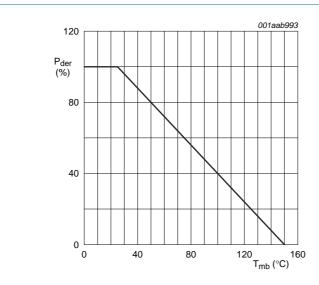
Type number	Package		
	Name	Description	Version
BUJ103AD	D-PAK	plastic single-ended surface mounted package; 3 leads (one lead cropped)	SOT428

# 4. Limiting values

### Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CESM}$	peak collector-emitter voltage	$V_{BE} = 0 V$	-	700	V
$V_{CBO}$	collector-base voltage	open emitter	-	700	V
$V_{CEO}$	collector-emitter voltage	open base	-	400	V
I <sub>C</sub>	collector current (DC)		-	4	Α
I <sub>CM</sub>	peak collector current		-	8	Α
$I_{B}$	base current (DC)		-	2	Α
$I_{BM}$	peak base current		-	4	Α
P <sub>tot</sub>	total power dissipation	$T_{mb} \le 25$ °C; see Figure 1	-	80	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	150	°C



$$P_{der}(\%) = \frac{P_{tot}}{P_{tot(25 °C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature

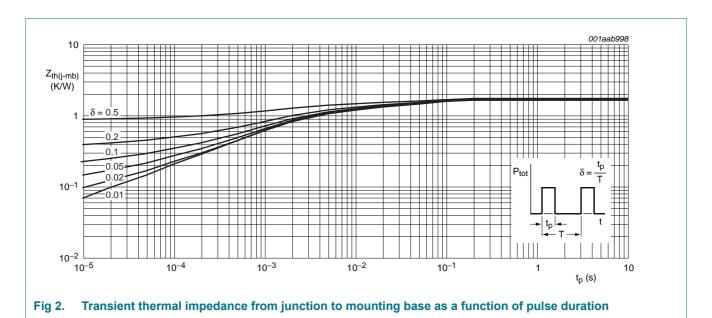


## 5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 2	-	-	1.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u> _	75	-	K/W

[1] Device mounted on a printed-circuit board; minimum footprint.



## 6. Characteristics

Table 5. Characteristics

 $T_{mb}$  = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
I <sub>CES</sub> collector-emitter cut-off	collector-emitter cut-off	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = V <sub>CESMmax</sub>	<u>[1]</u> _	-	1.0	mA
	current	$V_{BE} = 0 \text{ V}; V_{CE} = V_{CESMmax}; T_j = 125 ^{\circ}\text{C}$	<u>[1]</u> _	-	2.0	mA
I <sub>CBO</sub>	collector-base cut-off current	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = V <sub>CESMmax</sub>	<u>[1]</u> _	-	1.0	mA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CEO} = V_{CEOMmax} = 400 \text{ V}$	<u>[1]</u> _	-	0.1	mA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 7 \text{ V}; I_{C} = 0 \text{ A}$	-	-	0.1	mA
V <sub>CEOsus</sub>	collector-emitter sustaining voltage	$I_B = 0$ A; $I_C = 10$ mA; L = 25 mH; see Figure 3 and 4	400	-	-	V
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 3.0 \text{ A}$ ; $I_B = 0.6 \text{ A}$ ; see Figure 10	-	0.25	1.0	V
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = 3.0 \text{ A}$ ; $I_B = 0.6 \text{ A}$ ; see <u>Figure 11</u>	-	0.97	1.5	V
h <sub>FE</sub>	DC current gain	$I_C = 1 \text{ mA}$ ; $V_{CE} = 5 \text{ V}$ ; see <u>Figure 9</u>	10	17	32	
		$I_C = 500 \text{ mA}; V_{CE} = 5 \text{ V}$	13	22	32	

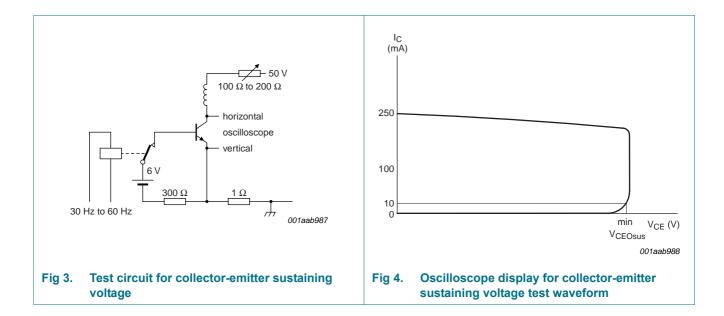
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Table 5. Characteristics ...continued

 $T_{mb} = 25$  °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
h <sub>FEsat</sub>	DC saturation current gain	$I_C = 2.0 \text{ A}; V_{CE} = 5 \text{ V}$	11	16	22	
		$I_C = 3.0 \text{ A}; V_{CE} = 5 \text{ V}$	-	12.5	-	
Dynamic o	haracteristics					
Switching t	imes (resistive load); see Figure	<u>5</u> and <u>6</u>				
t <sub>on</sub>	turn-on time	$I_{Con}$ = 2.5 A; $I_{Bon}$ = $-I_{Boff}$ = 0.5 A; $R_L$ = 75 $\Omega$	-	0.52	0.6	μS
t <sub>stg</sub>	storage time		-	2.7	3.3	μS
t <sub>f</sub>	fall time		-	0.3	0.35	μS
Switching t	imes (inductive load); see Figure	<u>e 7</u> and <u>8</u>				
t <sub>stg</sub>	storage time	$I_{Con} = 2 \text{ A}$ ; $I_{Bon} = 0.4 \text{ A}$ ; $L_{B} = 1 \mu \text{H}$ ;	-	1.2	1.4	μS
t <sub>f</sub>	fall time	$V_{BB} = -5 \text{ V}$	-	30	60	ns
Switching t	imes (inductive load); see Figure	<u>e 7</u> and <u>8</u>				
t <sub>stg</sub>	storage time	$I_{Con} = 2 \text{ A}; I_{Bon} = 0.4 \text{ A}; L_{B} = 1 \mu\text{H};$ $V_{BB} = -5 \text{ V}; T_{j} = 100 \text{ °C}$	-	-	1.8	μS
t <sub>f</sub>	fall time		-	-	120	ns

[1] Measured with half sine-wave voltage (curve tracer).

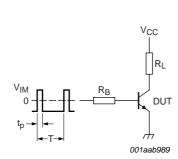


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 $\mathsf{I}_{\mathsf{Con}}$ 

### Silicon diffused power transistor



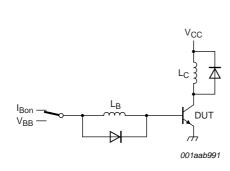
 $V_{IM}$  = -6 V to +8 V;  $V_{CC}$  = 250 V;  $t_p$  = 20  $\mu s;$   $\delta$  =  $t_p/T$  = 0.01.

 $R_{B}$  and  $R_{L}$  calculated from  $I_{Con}$  and  $I_{Bon}$  requirements.

# $I_{B}$ $t_{r} \leq 30 \text{ ns}$ $t_{r} \leq 30 \text{ ns}$ $t_{r} \leq 30 \text{ ns}$ $t_{r} \leq 30 \text{ ns}$

Fig 6. Switching times waveforms for resistive load

### Fig 5. Test circuit for resistive load switching



 $V_{CC}$  = 300 V;  $V_{BB}$  = –5 V;  $L_{C}$  = 200  $\mu H; \ L_{B}$  = 1  $\mu H.$ 

Fig 7. Test circuit for inductive load switching

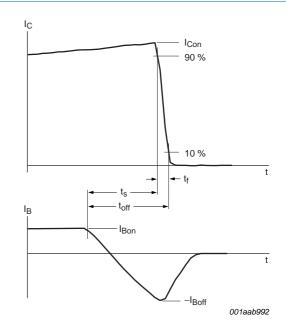


Fig 8. Switching times waveforms for inductive load

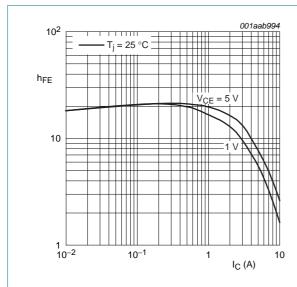


Fig 9. DC current gain as a function of collector current; typical values

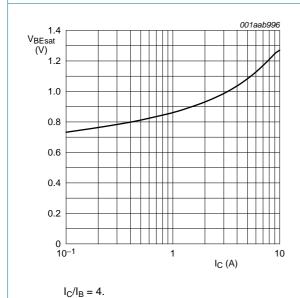
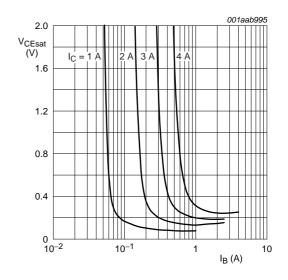
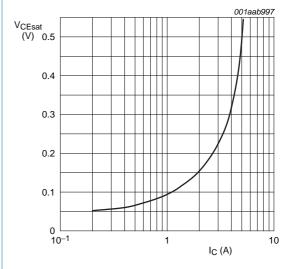


Fig 11. Base-emitter saturation voltage as a function of collector current; typical values



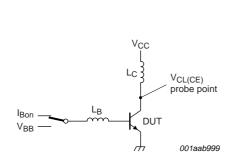
 $T_i = 25 \, ^{\circ}C$ .

Fig 10. Collector-emitter saturation voltage as a function of base current; typical values



 $I_{\rm C}/I_{\rm B}=4$ .

Fig 12. Collector-emitter saturation voltage as a function of collector current; typical values



 $V_{CEclamp} \leq 1000 \ V; \ V_{CC} = 150 \ V; \ V_{BB} = -5 \ V; \ L_B = 1 \ \mu H;$ 

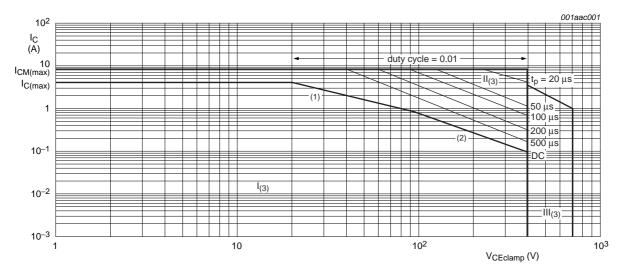
 $L_C = 200 \ \mu H.$ 

001aac000 10 I<sub>C</sub> 8 6 4 2 0 200 1000 V<sub>CEclamp</sub> (V)

 $T_j \leq T_{j(max)}.$ 

Fig 13. Test circuit for reverse bias safe operating

Fig 14. Reverse bias safe operating area



 $T_{mb}$   $\leq$  25 °C; Mounted with heatsink compound and 30  $\pm$  5 Newton force on the center of the envelope.

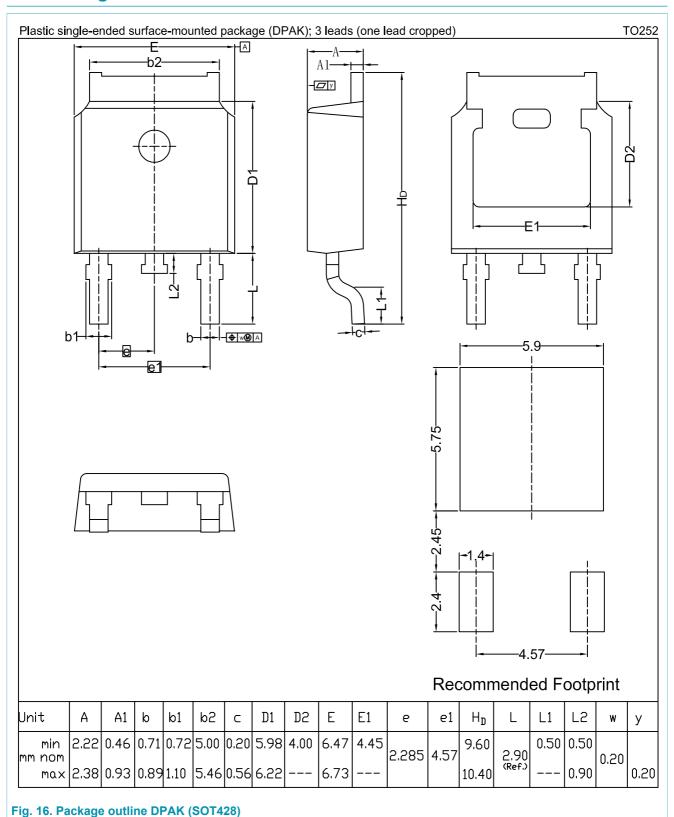
- (1) Ptot maximum and Ptot peak maximum lines.
- (2) Second breakdown limits.
- (3) I = Region of permissible DC operation.
  - II = Extension for repetitive pulse operation.
  - III = Extension during turn-on in single transistor converters provided that  $R_{BE} \le 100~\Omega$  and  $t_p \le 0.6~\mu s$ .

Fig 15. Forward bias safe operating area

### **Package information** 7.

Epoxy meets requirements of UL94 V-0 at ½ inch.

## 8. Package outline





## 9. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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